Highly-Efficient 140W Transistor Released for Volume Production

RF Micro Devices, Inc. announced that RFMD® has qualified and production released the RF3934, a 140-watt highly-efficient gallium nitride (GaN) RF unmatched power transistor (UPT) with superior performance versus competing GaAs and silicon power technologies.

RFMD's unmatched power transistors support "green" architectures that reduce energy consumption, improving thermal management and network efficiency for network operators. The RF3934 operates over a broad frequency range (DC to 3GHz) in a single amplifier design. The high peak efficiency of >65% minimizes thermal management demand and improves overall power consumption requirements for end customers.br>br> Additionally, ease of design implementation and integration is enhanced through the incorporation of simple, optimized matching networks external to the package, providing wideband gain and power performance advantages in a single amplifier. The RF3934 is packaged in a hermetic, flanged ceramic two-leaded package that leverages RFMD's advanced heat sink and power dissipation technologies to deliver excellent thermal stability and conductivity.br>br> The RF3934 is designed in RFMD's 48-volt high power-density GaN semiconductor process - featuring a unique combination of high RF power density and efficiency, low capacitance and high thermal conductivity. Such features enable the development of compact and efficient high power amplifiers (HPAs) for a broad range of applications, including public mobile radio (PMR), 3G/4G

wireless infrastructure, ISM (industrial scientific & medical), military and civilian radar and CATV transmission networks.br>br> The RF3934 is currently available for sampling and mass production. Product datasheets are available at http://www.rfmd.com/ br>br>

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